

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

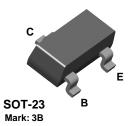
ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



PN918

MMBT918





NPN RF Transistor

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	3.0	V
I _C	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	M	Units	
		PN918	*MMBT918	
P _D	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
0550114	DA OTEDIOTION				
	RACTERISTICS		1 45	Т	1 1/
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage*	$I_C = 3.0 \text{ mA}, I_B = 0$	15		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 1.0 \mu A, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	3.0		V
СВО	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, I_{E} = 0$ $V_{CB} = 15 \text{ V}, T_{A} = 150^{\circ}\text{C}$		0.01 1.0	μA μA
ON CHAR	RACTERISTICS				
				7	
n _{FE}	DC Current Gain	I _C = 3.0 mA, V _{CE} = 1.0 V	20		
n _{FE}	DC Current Gain Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA	20	0.4	V
∩ _{FE} √ _{CE(sat)}	DC Current Gain		20	0.4	V
N _{FE} V _{CE(sat)} V _{BE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA	20		V
N _{FE} V _{CE(sat)} V _{BE(sat)} SMALL SI	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 4.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$		1.0	V
OFE /CE(sat) /BE(sat) SMALL SI	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage IGNAL CHARACTERISTICS	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 4.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		1.0	V V MHz
OFE /CE(sat) /BE(sat) SMALL SI T	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance	$\begin{split} I_C &= 10 \text{ mA}, \ I_B = 1.0 \text{ mA} \\ I_C &= 10 \text{ mA}, \ I_B = 1.0 \text{ mA} \\ \end{split}$ $\begin{split} I_C &= 4.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} V_{CB} &= 10 \text{ V}, \ I_E = 0, \ f = 1.0 \text{ MHz} \\ V_{CB} &= 0, \ I_E = 0, \ f = 1.0 \text{ MHz} \\ \end{split}$		1.7	MHz
h _{FE} V _{CE(sat)} V _{BE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 4.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		1.0	V V MHz

FUNCTIONAL TEST

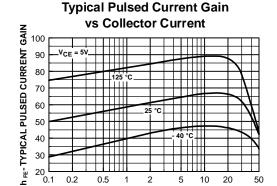
G _{pe}	Amplifier Power Gain	$V_{CB} = 12 \text{ V}, I_{C} = 6.0 \text{ mA},$ f = 200 MHz	15	dB	
Po	Power Output	$V_{CB} = 15 \text{ V}, I_{C} = 8.0 \text{ mA},$ f = 500 MHz	30	mW	/
η	Collector Efficiency	$V_{CB} = 15 \text{ V}, I_{C} = 8.0 \text{ mA},$ f = 500 MHz	25	%	

^{*}Pulse Test: Pulse Width $\leq\!300\,\mu\text{s},\,\text{Duty Cycle}\,\leq\!2.0\%$

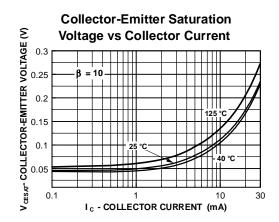
(continued)

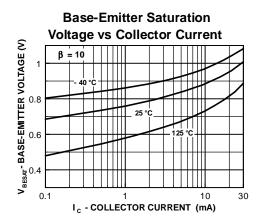
Typical Characteristics

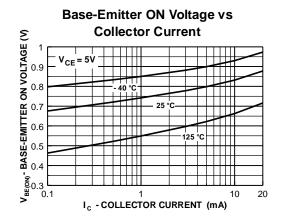
20 L 0.1

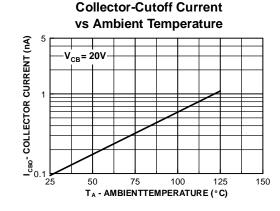


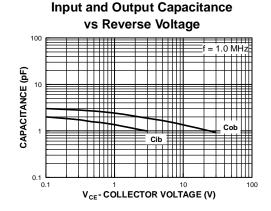
Ic - COLLECTOR CURRENT (mA)





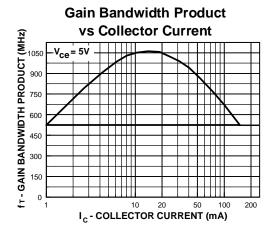




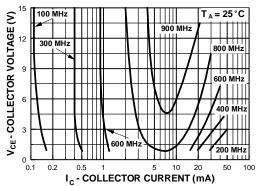


(continued)

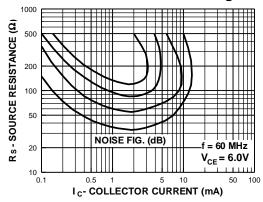
Typical Characteristics (continued)



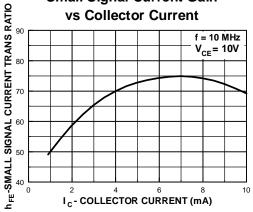
Contours of Constant Gain Bandwidth Product (f_T)



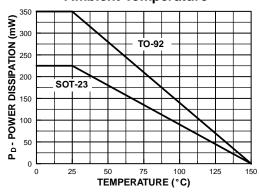




Small Signal Current Gain



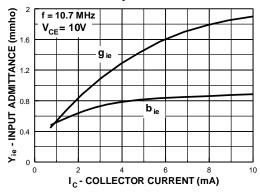
Power Dissipation vs Ambient Temperature



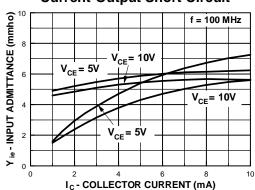
(continued)

Common Emitter Y Parameters vs. Frequency

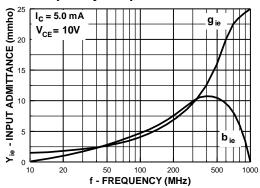
Input Admittance vs Collector Current-Output Short Circuit



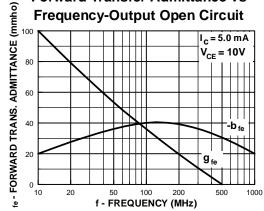
Input Admittance vs Collector **Current-Output Short Circuit**



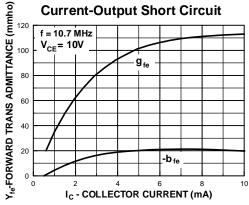
Input Admittance vs Frequency-Output Short Circuit



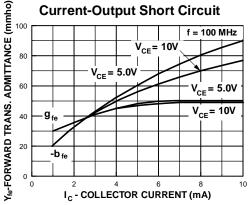
Forward Transfer Admittance vs **Frequency-Output Open Circuit**



Forward Trans. Admittance vs Collector



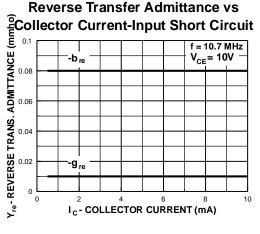
Forward Trans. Admittance vs Collector **Current-Output Short Circuit**



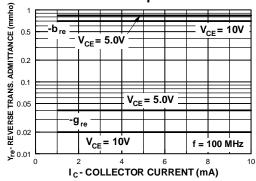
(continued)

Common Emitter Y Parameters vs. Frequency (continued)

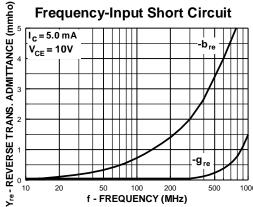
Reverse Transfer Admittance vs



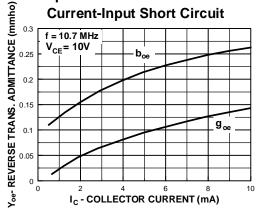
Reverse Transfer Admittance vs Collector Current-Input Short Circuit



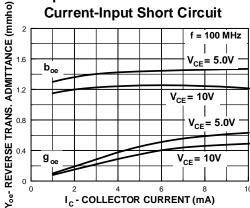
Reverse Transfer Admittance vs Frequency-Input Short Circuit



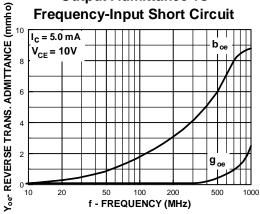
Output Admittance vs Collector Current-Input Short Circuit



Output Admittance vs Collector



Output Admittance vs Frequency-Input Short Circuit



(continued)

Test Circuit

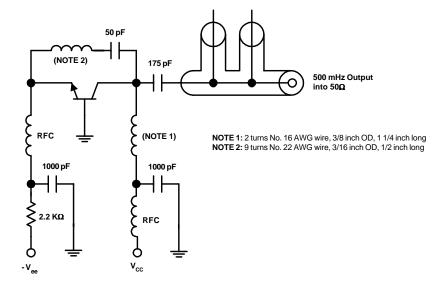


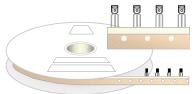
FIGURE 1: 500 MHz Oscillator Circuit

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

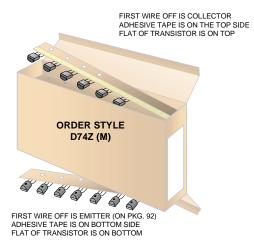


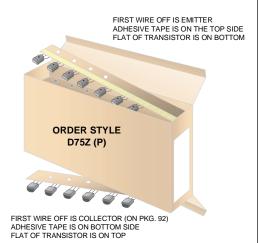
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





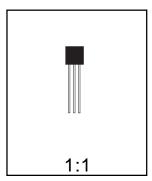


TO-92 Package Dimensions



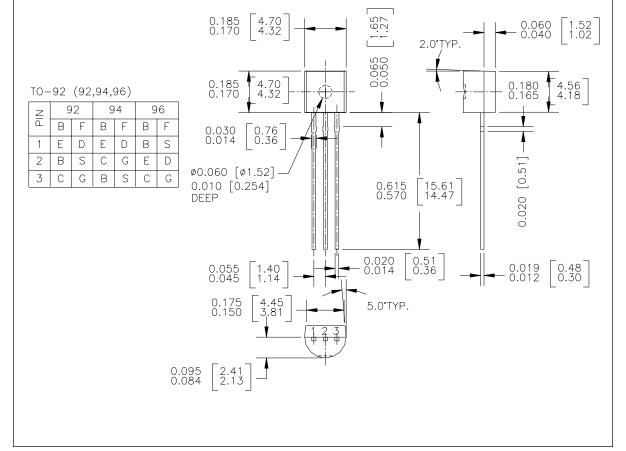
TO-92 (FS PKG Code 92, 94, 96)

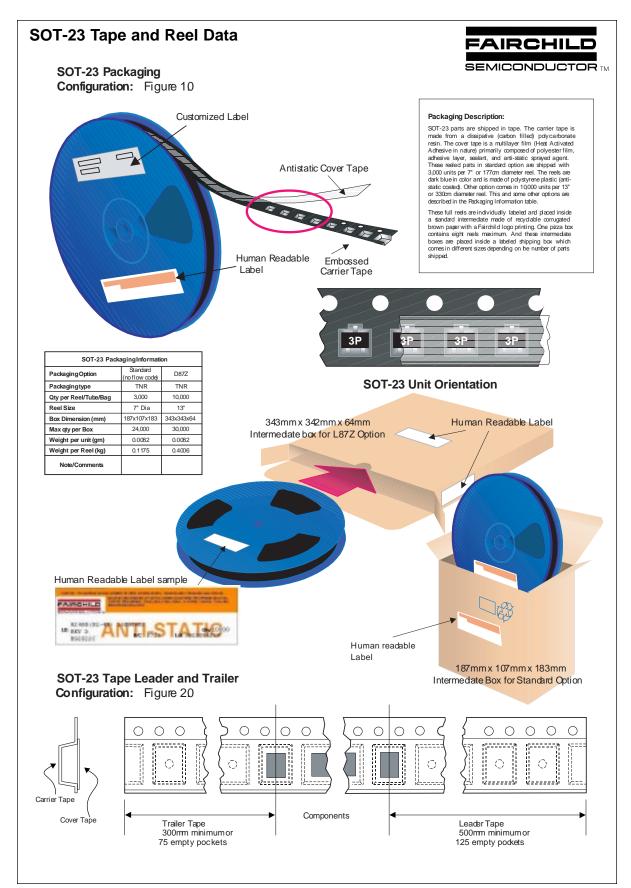




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

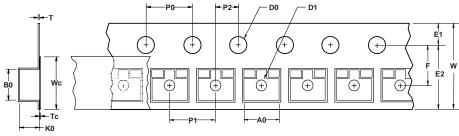




SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



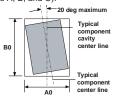
Use	er Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

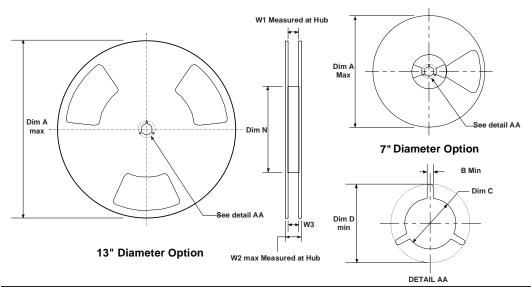


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

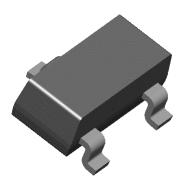
SOT-23 Reel Configuration: Figure 4.0

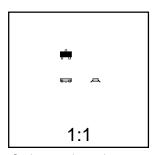


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



SOT-23 (FS PKG Code 49)

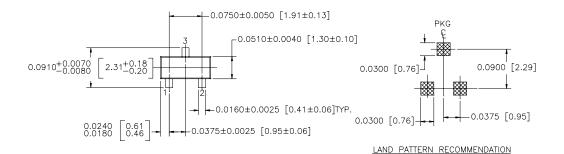


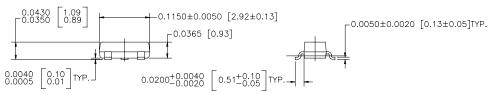


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS SOT 23, 3 LEADS LOW PROFILE

NOTE : UNLESS OTHERWISE SPECIFIED

- STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

 $ACEx^{TM}$ FASTr™ PowerTrench® SyncFET™ Bottomless™ QFET™ TinyLogic™ GlobalOptoisolator™ QSTM UHC™ CoolFET™ GTO™ **VCX**TM $CROSSVOLT^{TM}$ QT Optoelectronics™ HiSeC™

DOME™ ISOPLANAR™ Quiet Series™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see any inability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and ex

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: MMBT918